Chih-Chung C C Yang

List of Publications by Year in Descending Order

258 papers	4,656 citations	38 h-index	55 g-index
303 ext. papers	5,232 ext. citations	3 avg, IF	5.07 L-index

#	Paper	IF	Citations
258	Enhancing deep-UV emission at 234 nm by introducing a truncated pyramid AlN/GaN nanostructure with fine-tuned multiple facets.. *Nanoscale*, **2022**, 14, 653-662	7.7	2
257	Hole mobility behavior in Al-gradient polarization-induced p-type AlGaN grown on GaN template. *Applied Physics Letters*, **2022**, 120, 022103	3.4	0
256	Surface plasmon coupling effects on the fÖster resonance energy transfer from quantum dot into rhodamine 6G. *Nanotechnology*, **2021**, 32,	3.4	3
255	Wide range variation of resonance wavelength of GaZnO plasmonic metamaterials grown by molecular beam epitaxy with slight modification of Zn effusion cell temperatures. *Journal of Alloys and Compounds*, **2021**, 870, 159434	5.7	3
254	Improvement of p-Type AlGaN Conductivity with an Alternating Mg-Doped/Un-Doped AlGaN Layer Structure. *Micromachines*, **2021**, 12,	3.3	2
253	Film Thickness Dependence of Surface Plasmon Resonance Behavior at a Grating Structure of Highly Ga-Doped ZnO. *Physica Status Solidi (A) Applications and Materials Science*, **2021**, 218, 2000150	1.6	
252	FÖster resonance energy transfer in surface plasmon coupled color conversion processes of colloidal quantum dots. *Optics Express*, **2021**, 29, 4067-4081	3.3	2
251	Combined effects of surface plasmon coupling and FÖster resonance energy transfer on the light color conversion behaviors of colloidal quantum dots on an InGaN/GaN quantum-well nanodisk structure. *Nanotechnology*, **2021**, 32, 135206	3.4	4
250	Growth Mechanism of InP Nanostructure Arrays by Self-Catalyzed Selective Area Epitaxy: A Deep Understanding of Thermodynamic and Kinetic Theories. *Crystal Growth and Design*, **2021**, 21, 988-994	3.5	1
249	Surface Plasmon Resonance-Induced Diffusion-Limited Aggregation in the Formation of Ag/AgOx Nanonetworks as Broad-Spectrum Transparent Conductors. *ACS Applied Nano Materials*, **2020**, 3, 11399-11407	5.6	1
248	Spatial range of the plasmonic Dicke effect in an InGaN/GaN multiple quantum well structure. *Nanotechnology*, **2020**, 31, 295001	3.4	4
247	Theoretical analysis of a white-light LED array based on a GaN nanorod structure. *Applied Optics*, **2020**, 59, 2345-2351	1.7	0
246	Important role of surface plasmon coupling with the quantum wells in a surface plasmon enhanced color-converting structure of colloidal quantum dots on quantum wells. *Optics Express*, **2020**, 28, 13352-13367	3.3	0
245	Emission behaviors of colloidal quantum dots linked onto synthesized metal nanoparticles. *Nanotechnology*, **2020**, 31, 095201	3.4	4
244	Highly-Conductive, Transparent Ga-Doped ZnO Nanoneedles for Improving the Efficiencies of GaN Light-Emitting Diode and Si Solar Cell. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 015002	2	2
243	Effects of Surface Plasmon Coupling on the Whispering-Gallery Resonance in a Hexagonal Nanowire Cavity Structure. *Plasmonics*, **2020**, 15, 39-49	2.4	2
242	Formation of Surface Silver Nano-network Structures through Hot Electron Regulated Diffusion-limited Aggregation. *Scientific Reports*, **2019**, 9, 6997	4.9	3

241	AlGaN nano-shell structure on a GaN nanorod formed with the pulsed MOCVD growth. *Nanotechnology*, **2019**, 30, 275201	3.4	3
240	Simulation study on light color conversion enhancement through surface plasmon coupling. *Optics Express*, **2019**, 27, A629-A642	3.3	8
239	Color conversion efficiency enhancement of colloidal quantum dot through its linkage with synthesized metal nanoparticle on a blue light-emitting diode. *Optics Letters*, **2019**, 44, 5691-5694	3	9
238	Surface plasmon resonance behaviors of a highly Ga-doped ZnO nano-grating structure. *Optical Materials Express*, **2019**, 9, 1826	2.6	4
237	Control of pore structure in a porous gold nanoparticle for effective cancer cell damage. *Nanotechnology*, **2019**, 30, 025101	3.4	3
236	Exocytosis of gold nanoparticle and photosensitizer from cancer cells and their effects on photodynamic and photothermal processes. *Nanotechnology*, **2018**, 29, 235101	3.4	5
235	Enhancement of Emission Efficiency of Deep-Ultraviolet AlGaN Quantum Wells Through Surface Plasmon Coupling with an Al Nanograting Structure. *Plasmonics*, **2018**, 13, 863-872	2.4	7
234	Different surface plasmon coupling behaviors of a surface Al nanoparticle between TE and TM polarizations in a deep-UV light-emitting diode. *Optics Express*, **2018**, 26, 8340-8355	3.3	7
233	Coupling of a light-emitting diode with surface plasmon polariton or localized surface plasmon induced on surface silver gratings of different geometries. *Optics Express*, **2018**, 26, 9205-9219	3.3	7
232	Resonance Behaviors of Localized Surface Plasmon on an Ag/GaN Nano-Grating Interface for Light-Emitting Diode Application. *Plasmonics*, **2018**, 13, 2293-2304	2.4	1
231	Further emission efficiency improvement of a commercial-quality light-emitting diode through surface plasmon coupling. *Optics Letters*, **2018**, 43, 5631-5634	3	10
230	Polarity Control in Growing Highly Ga-Doped ZnO Nanowires with the Vapor-Liquid-Solid Process. *ACS Applied Materials & Interfaces*, **2018**, 10, 40764-40772	9.5	6
229	Enhancements of Cancer Cell Damage Efficiencies in Photothermal and Photodynamic Processes through Cell Perforation and Preheating with Surface Plasmon Resonance of Gold Nanoring. *Molecules*, **2018**, 23,	4.8	3
228	Current penetration depth and effective conductivity of a nano-scale p-GaN/u-GaN alternating-layer p-type structure. *Superlattices and Microstructures*, **2018**, 124, 107-112	2.8	1
227	Direct observation of conduction band plasmons and the related Burstein-Moss shift in highly doped semiconductors: A STEM-EELS study of Ga-doped ZnO. *Physical Review B*, **2018**, 98,	3.3	14
226	Efficiency enhancement of light color conversion through surface plasmon coupling. *Optics Express*, **2018**, 26, 23629-23640	3.3	14
225	Growth Model of a GaN Nanorod with the Pulsed-Growth Technique of Metalorganic Chemical Vapor Deposition. *Crystal Growth and Design*, **2018**, 18, 3767-3773	3.5	6
224	Cancer cell death pathways caused by photothermal and photodynamic effects through gold nanoring induced surface plasmon resonance. *Nanotechnology*, **2017**, 28, 275101	3.4	3

223	Structure variation of a sidewall quantum well on a GaN nanorod. *Nanotechnology*, **2017**, 28, 045203	3.4	4
222	Combining High Hole Concentration in p-GaN and High Mobility in u-GaN for High p-Type Conductivity in a p-GaN/u-GaN Alternating-Layer Nanostructure. *IEEE Transactions on Electron Devices*, **2017**, 64, 115-120	2.9	8
221	Enhancing the Hole-Injection Efficiency of a Light-Emitting Diode by Increasing Mg Doping in the p-AlGaN Electron-Blocking Layer. *IEEE Transactions on Electron Devices*, **2017**, 64, 3226-3233	2.9	6
220	Dependencies of surface plasmon coupling effects on the p-GaN thickness of a thin-p-type light-emitting diode. *Optics Express*, **2017**, 25, 21526-21536	3.3	22
219	Method for enhancing the favored transverse-electric-polarized emission of an AlGaN deep-ultraviolet quantum well. *Optics Express*, **2017**, 25, 26365-26377	3.3	10
218	Anti-reflection behavior of a surface Ga-doped ZnO nanoneedle structure and the controlling factors. *Optical Materials Express*, **2017**, 7, 4058	2.6	9
217	Regularly patterned multi-section GaN nanorod arrays grown with a pulsed growth technique. *Nanotechnology*, **2016**, 27, 025303	3.4	10
216	Combination of photothermal and photodynamic inactivation of cancer cells through surface plasmon resonance of a gold nanoring. *Nanotechnology*, **2016**, 27, 115102	3.4	32
215	High Modulation Bandwidth of a Light-Emitting Diode With Surface Plasmon Coupling. *IEEE Transactions on Electron Devices*, **2016**, 63, 3989-3995	2.9	14
214	Direct measurement of defect and dopant abruptness at high electron mobility ZnO homojunctions. *Applied Physics Letters*, **2016**, 109, 143506	3.4	5
213	Sensitized TiO2 nanocomposites through HMME linkage for photodynamic effects. *Journal of Biomedical Optics*, **2016**, 21, 128001	3.5	7
212	Coupling Behaviors of Surface Plasmon Polariton and Localized Surface Plasmon with an InGaN/GaN Quantum Well. *Plasmonics*, **2016**, 11, 931-939	2.4	7
211	Coupling Behaviors of a Radiating Dipole with the Surface Plasmon Induced on a Metal Protrusion. *Plasmonics*, **2015**, 10, 241-249	2.4	5
210	Behaviors of Surface Plasmon Coupled Light-Emitting Diodes Induced by Surface Ag Nanoparticles on Dielectric Interlayers. *Plasmonics*, **2015**, 10, 1029-1040	2.4	8
209	Significant mobility enhancement in extremely thin highly doped ZnO films. *Applied Physics Letters*, **2015**, 106, 152102	3.4	10
208	Growth of Highly Conductive Ga-Doped ZnO Nanoneedles. *ACS Applied Materials & Interfaces*, **2015**, 7, 10525-33	9.5	21
207	Modulation behaviors of surface plasmon coupled light-emitting diode. *Optics Express*, **2015**, 23, 8150-61	3.3	28
206	Thermally induced variations of strain condition and emission behavior in flat and bendable light-emitting diodes on different substrates. *Optics Express*, **2015**, 23, 15491-503	3.3	1

205	Multi-section core-shell InGaN/GaN quantum-well nanorod light-emitting diode array. *Optics Express*, **2015**, 23, 21919-30	3.3	16
204	Surface plasmon coupling for suppressing p-GaN absorption and TM-polarized emission in a deep-UV light-emitting diode. *Optics Letters*, **2015**, 40, 4229-32	3	11
203	Evaluating the blue-shift behaviors of the surface plasmon coupling of an embedded light emitter with a surface Ag nanoparticle by adding a dielectric interlayer or coating. *Optics Express*, **2015**, 23, 30709-20	3.3	11
202	Photothermal Behaviors of Flowing Media Caused by Localized Surface Plasmon Resonance of Au Nanorings. *Plasmonics*, **2015**, 10, 1565-1572	2.4	
201	Sacrificial Structure for Effective Sapphire Substrate Liftoff Based on Photoelectrochemical Etching. *IEEE Photonics Technology Letters*, **2015**, 27, 770-773	2.2	2
200	Thermal Annealing Effects on the Performance of a Ga-Doped ZnO Transparent-Conductor Layer in a Light-Emitting Diode. *IEEE Transactions on Electron Devices*, **2015**, 62, 3742-3749	2.9	11
199	Multi-mechanism efficiency enhancement in growing Ga-doped ZnO as the transparent conductor on a light-emitting diode. *Optics Express*, **2015**, 23, 32274-88	3.3	9
198	Surface plasmon coupled light-emitting diode: Experimental and numerical studies. *Japanese Journal of Applied Physics*, **2015**, 54, 02BD01	1.4	8
197	Cancer cell uptake behavior of Au nanoring and its localized surface plasmon resonance induced cell inactivation. *Nanotechnology*, **2015**, 26, 075102	3.4	13
196	InGaN/GaN MQW Photoluminescence Enhancement by Localized Surface Plasmon Resonance on Isolated Ag Nanoparticles. *Plasmonics*, **2014**, 9, 1183-1187	2.4	5
195	Regularly patterned non-polar InGaN/GaN quantum-well nanorod light-emitting diode array. *Optics Express*, **2014**, 22 Suppl 7, A1799-809	3.3	25
194	Defect study of GaN based LED structure by electron beam induced current. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 734-737		
193	Thermal Effects in a Bendable InGaN/GaN Quantum-Well Light-Emitting Diode. *IEEE Photonics Technology Letters*, **2014**, 26, 1442-1445	2.2	2
192	Extraordinary N atom tunneling in formation of InN shell layer on GaN nanorod m-plane sidewall. *Nanotechnology*, **2014**, 25, 495705	3.4	
191	Void Structures in Regularly Patterned ZnO Nanorods Grown with the Hydrothermal Method. *Journal of Nanomaterials*, **2014**, 2014, 1-11	3.2	2
190	Enhancements of the emission and light extraction of a radiating dipole coupled with localized surface plasmon induced on a surface metal nanoparticle in a light-emitting device. *Optics Express*, **2014**, 22 Suppl 1, A155-66	3.3	25
189	Phosphor-free, white-light LED under alternating-current operation. *Optics Letters*, **2014**, 39, 6371-4	3	6
188	Independent variations of applied voltage and injection current for controlling the quantum-confined Stark effect in an InGaN/GaN quantum-well light-emitting diode. *Optics Express*, **2014**, 22, 8367-75	3.3	8

187	Efficiency improvement of a vertical light-emitting diode through surface plasmon coupling and grating scattering. *Optics Express*, **2014**, 22 Suppl 3, A842-56	3.3	37
186	Photothermal optical coherence tomography based on the localized surface plasmon resonance of Au nanoring. *Optics Express*, **2014**, 22, 11754-69	3.3	13
185	Dependencies of the emission behavior and quantum well structure of a regularly-patterned, InGaN/GaN quantum-well nanorod array on growth condition. *Optics Express*, **2014**, 22, 17303-19	3.3	17
184	Temperature dependent double blueshift of photoluminescence peak position in MgZnO epitaxial layers. *Journal of Applied Physics*, **2014**, 116, 123501	2.5	10
183	Further reduction of efficiency droop effect by adding a lower-index dielectric interlayer in a surface plasmon coupled blue light-emitting diode with surface metal nanoparticles. *Applied Physics Letters*, **2014**, 105, 101106	3.4	34
182	Localized Surface Plasmon Coupled Light-Emitting Diodes With Buried and Surface Ag Nanoparticles. *IEEE Photonics Technology Letters*, **2014**, 26, 1699-1702	2.2	3
181	Spatially resolved study of InGaN photoluminescence enhancement by single Ag nanoparticles. *Journal Physics D: Applied Physics*, **2013**, 46, 145105	3	4
180	Surface plasmon coupling with a radiating dipole near a Ag nanoparticle embedded in GaN. *Applied Physics Letters*, **2013**, 102, 161103	3.4	27
179	On-substrate fabrication of a bio-conjugated Au nanoring solution for photothermal therapy application. *Nanotechnology*, **2013**, 24, 065102	3.4	13
178	Vertical CdZnO/ZnO Quantum-Well Light-Emitting Diode. *IEEE Photonics Technology Letters*, **2013**, 25, 317-319	2.2	4
177	Light-emitting device with regularly patterned growth of an InGaN/GaN quantum-well nanorod light-emitting diode array. *Optics Letters*, **2013**, 38, 3370-3	3	30
176	Surface-plasmon-coupled emission enhancement of a quantum well with a metal nanoparticle embedded in a light-emitting diode. *Journal of the Optical Society of America B: Optical Physics*, **2013**, 30, 2599	1.7	21
175	Vertical light-emitting diodes with surface gratings and rough surfaces for effective light extraction. *Optics Express*, **2013**, 21, 17686-94	3.3	16
174	Surface plasmon coupled light-emitting diode with metal protrusions into p-GaN. *Applied Physics Letters*, **2013**, 102, 041108	3.4	48
173	Noninvasive imaging of heart chamber in Drosophila with dual-beam optical coherence tomography. *Journal of Biophotonics*, **2013**, 6, 708-17	3.1	10
172	Strain reduction and crystal improvement of an InGaN/GaN quantum-well light-emitting diode on patterned Si (110) substrate. *Applied Physics Letters*, **2013**, 103, 141914	3.4	4
171	Differentiation of oral precancerous stages with optical coherence tomography based on the evaluation of optical scattering properties of oral mucosae. *Laser Physics*, **2013**, 23, 045602	1.2	4
170	Cross-sectional sizes and emission wavelengths of regularly patterned GaN and core-shell InGaN/GaN quantum-well nanorod arrays. *Journal of Applied Physics*, **2013**, 113, 054315	2.5	33

169	Unintentional annealing of the active layer in the growth of InGaN/GaN quantum well light-emitting diode structures. *Physica Status Solidi (A) Applications and Materials Science*, **2013**, 210, 1657-1662	1.6	
168	Photoelectrochemical Liftoff of Patterned Sapphire Substrate for Fabricating Vertical Light-Emitting Diode. *IEEE Photonics Technology Letters*, **2012**, 24, 1775-1777	2.2	12
167	MBE-Grown CdZnO/ZnO Multiple Quantum-Well Light-Emitting Diode on MOCVD-Grown p-Type GaN. *IEEE Photonics Technology Letters*, **2012**, 24, 909-911	2.2	8
166	Comparison of emission characteristics between the CdZnO/ZnO quantum wells on ZnO and GaN templates. *Optics Express*, **2012**, 20, 21860-74	3.3	4
165	Suppression of defect-related luminescence in laser-annealed InGaN epilayers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 1021-1023		1
164	Differential gene expression between the porcine morula and blastocyst. *Reproduction in Domestic Animals*, **2012**, 47, 69-81	1.6	4
163	Crystallinity Improvement of ZnO Thin Film on Different Buffer Layers Grown by MBE. *Journal of Nanomaterials*, **2012**, 2012, 1-7	3.2	25
162	Diagnosis of oral precancer with optical coherence tomography. *Biomedical Optics Express*, **2012**, 3, 1632-46	3.5	49
161	Computation time-saving mirror image suppression method in Fourier-domain optical coherence tomography. *Optics Express*, **2012**, 20, 8270-83	3.3	7
160	Surface plasmon effects in the absorption enhancements of amorphous silicon solar cells with periodical metal nanowall and nanopillar structures. *Optics Express*, **2012**, 20, A104-18	3.3	27
159	Effects of overgrown p-layer on the emission characteristics of the InGaN/GaN quantum wells in a high-indium light-emitting diode. *Optics Express*, **2012**, 20, 11321-35	3.3	15
158	Geometry and composition comparisons between c-plane disc-like and m-plane core-shell InGaN/GaN quantum wells in a nitride nanorod. *Optics Express*, **2012**, 20, 15859-71	3.3	39
157	Two-reference swept-source optical coherence tomography of high operation flexibility. *Optics Express*, **2012**, 20, 28418-30	3.3	2
156	Bond lengths and lattice structure of InP0.52Sb0.48 grown on GaAs. *Applied Physics Letters*, **2012**, 101, 091902	3.4	9
155	Spiral Deposition with Alternating Indium Composition in Growing an InGaN Nanoneedle with the Vapor-Liquid-Solid Growth Mode. *Journal of Nanomaterials*, **2012**, 2012, 1-7	3.2	
154	Surface plasmon coupling with radiating dipole for enhancing the emission efficiency of a light-emitting diode. *Optics Express*, **2011**, 19 Suppl 4, A914-29	3.3	46
153	Motion-insensitive optical coherence tomography based micro-angiography. *Optics Express*, **2011**, 19, 26117-31	3.3	4
152	Method for suppressing the mirror image in Fourier-domain optical coherence tomography. *Optics Letters*, **2011**, 36, 2889-91	3	8

151	Microvascular Imaging Using Swept-Source Optical Coherence Tomography with Single-Channel Acquisition. *Applied Physics Express*, **2011**, 4, 097001	2.4	12
150	Geometry for Maximizing Localized Surface Plasmon Resonance of Au Nanorings with Random Orientations. *Plasmonics*, **2011**, 6, 547-555	2.4	9
149	Observations of cardiac beating behaviors of wild-type and mutant Drosophilae with optical coherence tomography. *Journal of Biophotonics*, **2011**, 4, 610-8	3.1	8
148	Emission Efficiency Dependence on the p-GaN Thickness in a High-Indium InGaN/GaN Quantum-Well Light-Emitting Diode. *IEEE Photonics Technology Letters*, **2011**, 23, 1757-1759	2.2	4
147	Sapphire Substrate Liftoff With Photoelectrochemical Etching for Vertical Light-Emitting Diode Fabrication. *IEEE Photonics Technology Letters*, **2011**, 23, 654-656	2.2	10
146	Fabrication of surface metal nanoparticles and their induced surface plasmon coupling with subsurface InGaN/GaN quantum wells. *Nanotechnology*, **2011**, 22, 475201	3.4	22
145	A GaN photonic crystal membrane laser. *Nanotechnology*, **2011**, 22, 025201	3.4	21
144	Effects of the intermediate SiO2 layer on polarized output of a light-emitting diode with surface plasmon coupling. *Journal of Applied Physics*, **2010**, 108, 113101	2.5	26
143	Reduction in the efficiency droop effect of a light-emitting diode through surface plasmon coupling. *Applied Physics Letters*, **2010**, 96, 261104	3.4	52
142	Visfatin regulates genes related to lipid metabolism in porcine adipocytes. *Journal of Animal Science*, **2010**, 88, 3233-41	0.7	20
141	Au nanorings for enhancing absorption and backscattering monitored with optical coherence tomography. *Nanotechnology*, **2010**, 21, 295102	3.4	28
140	Emission characteristics of organic light-emitting diodes and organic thin-films with planar and corrugated structures. *International Journal of Molecular Sciences*, **2010**, 11, 1527-45	6.3	53
139	Light Extraction Enhancement of a GaN-Based Light-Emitting Diode Through Grating-Patterned Photoelectrochemical Surface Etching With Phase Mask Interferometry. *IEEE Photonics Technology Letters*, **2010**, 22, 640-642	2.2	14
138	Characterizing the localized surface plasmon resonance behaviors of Au nanorings and tracking their diffusion in bio-tissue with optical coherence tomography. *Biomedical Optics Express*, **2010**, 1, 1060-1073	3.5	23
137	Enhancing InGaN-based solar cell efficiency through localized surface plasmon interaction by embedding Ag nanoparticles in the absorbing layer. *Optics Express*, **2010**, 18, 2682-94	3.3	53
136	Absorption enhancement of an amorphous Si solar cell through surface plasmon-induced scattering with metal nanoparticles. *Optics Express*, **2010**, 18 Suppl 2, A207-20	3.3	58
135	Nitride Nanocolumns for the Development of Light-Emitting Diode. *IEEE Transactions on Electron Devices*, **2010**, 57, 71-78	2.9	20
134	Carrier dynamics in GaN layers overgrown on nanocolumnar structures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 1856-1858		

133	Improving emission enhancement in surface plasmon coupling with an InGaN/GaN quantum well by inserting a dielectric layer of low refractive index between metal and semiconductor. *Applied Physics Letters*, **2009**, 94, 233113	3.4	30
132	Impact of high-order surface plasmon modes of metal nanoparticles on enhancement of optical emission. *Applied Physics Letters*, **2009**, 95, 171103	3.4	51
131	Coalescence overgrowth of GaN nanocolumns on sapphire with patterned metal organic vapor phase epitaxy. *Journal of Applied Physics*, **2009**, 105, 023501	2.5	47
130	Characterizations of GaN-Based LEDs Encompassed With Self-Aligned Nanorod Arrays of Various Distribution Densities. *IEEE Electron Device Letters*, **2009**, 30, 1060-1062	4.4	6
129	Effective energy coupling and preservation in a surface plasmon-light emitter coupling system on a metal nanostructure. *Nanotechnology*, **2009**, 20, 135202	3.4	1
128	Ultrafast Exciton Dynamics in a ZnO Thin Film. *Japanese Journal of Applied Physics*, **2009**, 48, 022402	1.4	5
127	Differentiating oral lesions in different carcinogenesis stages with optical coherence tomography. *Journal of Biomedical Optics*, **2009**, 14, 044028	3.5	61
126	Phosphor-Free Monolithic White-Light LED. *IEEE Journal of Selected Topics in Quantum Electronics*, **2009**, 15, 1210-1217	3.8	35
125	Photoluminescence studies of MBE-grown ZnO and MgZnO epitaxial layers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 2668-2670		4
124	Threading dislocation evolution in patterned GaN nanocolumn growth and coalescence overgrowth. *Journal of Applied Physics*, **2009**, 106, 023521	2.5	38
123	Characteristics of light emitter coupling with surface plasmons in air/metal/dielectric grating structures. *Journal of the Optical Society of America B: Optical Physics*, **2009**, 26, 923	1.7	5
122	Study on the decay mechanisms of surface plasmon coupling features with a light emitter through time-resolved simulations. *Optics Express*, **2009**, 17, 104-16	3.3	4
121	Fabrication of sphere-like Au nanoparticles on substrate with laser irradiation and their polarized localized surface plasmon behaviors. *Optics Express*, **2009**, 17, 14186-98	3.3	32
120	Diagnosis of oral submucous fibrosis with optical coherence tomography. *Journal of Biomedical Optics*, **2009**, 14, 054008	3.5	31
119	Twenty-three new microsatellite loci in the stable fly, Stomoxys calcitrans (L.) (Diptera: Muscidae). *Molecular Ecology Resources*, **2009**, 9, 271-3	8.4	
118	Clinical diagnosis of oral submucous fibrosis with optical coherence tomography **2009**,		2
117	Dependence of spectral behavior in an InGaN/GaN quantum-well light-emitting diode on the prestrained barrier thickness. *Journal of Applied Physics*, **2008**, 104, 043108	2.5	15
116	Delineation of an oral cancer lesion with swept-source optical coherence tomography. *Journal of Biomedical Optics*, **2008**, 13, 044012	3.5	40

115	Polarization dependent coupling of surface plasmon on a one-dimensional Ag grating with an InGaN□GaN dual-quantum-well structure. *Applied Physics Letters*, **2008**, 92, 013108	3.4	28
114	Numerical Study on Quantum Efficiency Enhancement of a Light-Emitting Diode Based on Surface Plasmon Coupling With a Quantum Well. *IEEE Photonics Technology Letters*, **2008**, 20, 1339-1341	2.2	12
113	Improved a-plane GaN quality grown with flow modulation epitaxy and epitaxial lateral overgrowth on r-plane sapphire substrate. *Applied Physics Letters*, **2008**, 92, 231902	3.4	18
112	Measurement of the hemoglobin oxygen saturation level with spectroscopic spectral-domain optical coherence tomography. *Optics Letters*, **2008**, 33, 416-8	3	46
111	Effective indicators for diagnosis of oral cancer using optical coherence tomography. *Optics Express* , **2008**, 16, 15847-62	3.3	93
110	Improvement of External Extraction Efficiency in GaN-Based LEDs by $ hbox{SiO}_{2}$ Nanosphere Lithography. *IEEE Electron Device Letters*, **2008**, 29, 658-660	4.4	44
109	High-phase-purity zinc-blende InN on r-plane sapphire substrate with controlled nitridation pretreatment. *Applied Physics Letters*, **2008**, 92, 111914	3.4	21
108	Enhanced efficiency and reduced spectral shift of green light-emitting-diode epitaxial structure with prestrained growth. *Journal of Applied Physics*, **2008**, 104, 123106	2.5	41
107	Transient behaviors of surface plasmon coupling with a light emitter. *Applied Physics Letters*, **2008**, 93, 153104	3.4	3
106	Localized surface plasmon-induced emission enhancement of a green light-emitting diode. *Nanotechnology*, **2008**, 19, 345201	3.4	144
105	Enhanced and partially polarized output of a light-emitting diode with its InGaN/GaN quantum well coupled with surface plasmons on a metal grating. *Applied Physics Letters*, **2008**, 93, 231111	3.4	55
104	White-light light-emitting device based on surface plasmon-enhanced CdSe⁄ZnS nanocrystal wavelength conversion on a blue/green two-color light-emitting diode. *Applied Physics Letters*, **2008**, 92, 091112	3.4	28
103	Differentiating the contributions between localized surface plasmon and surface plasmon polariton on a one-dimensional metal grating in coupling with a light emitter. *Applied Physics Letters*, **2008**, 92, 133115	3.4	24
102	Fabrication of photonic crystal light-emitting diode with photoelectrochemical wet etching and phase mask interference **2008**,		1
101	Reduced injection current induced blueshift in an InGaN□GaN quantum-well light-emitting diode of prestrained growth. *Applied Physics Letters*, **2007**, 91, 051121	3.4	46
100	Influence of the quantum-confined Stark effect in an InGaN□GaN quantum well on its coupling with surface plasmon for light emission enhancement. *Applied Physics Letters*, **2007**, 90, 183114	3.4	35
99	Uncertainty of Positioning and Displacement Measurements in Quantum and Thermal Regimes. *IEEE Transactions on Instrumentation and Measurement*, **2007**, 56, 1658-1665	5.2	8
98	Epitaxial overgrowth of GaN nanocolumns. *Journal of Vacuum Science & Technology B*, **2007**, 25, 964		15

97	Formation of various metal nanostructures with thermal annealing to control the effective coupling energy between a surface plasmon and an InGaN/GaN quantum well. *Nanotechnology*, **2007**, 18, 265402	3.4	40
96	Coalescence overgrowth of GaN nano-columns with metalorganic chemical vapor deposition. *Nanotechnology*, **2007**, 18, 445601	3.4	11
95	Residual thermal strain in thick GaN epifilms revealed by cross-sectional Raman scattering and cathodoluminescence spectra. *Semiconductor Science and Technology*, **2007**, 22, 896-899	1.8	37
94	X-ray diffraction study on an InGaN□GaN quantum-well structure of prestrained growth. *Journal of Applied Physics*, **2007**, 101, 113503	2.5	16
93	Surface plasmon coupling effect in an InGaN□GaN single-quantum-well light-emitting diode. *Applied Physics Letters*, **2007**, 91, 171103	3.4	109
92	Carrier trapping effects on photoluminescence decay time in InGaN□GaN quantum wells with nanocluster structures. *Journal of Applied Physics*, **2007**, 101, 063511	2.5	12
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